Srinivasan Krishnamurthy

List of Publications by Year
in descending order

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30	819	516710 16	477307 29
papers	citations	h-index	g-index

30	30	30	628
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Accurate evaluation of nonlinear absorption coefficients in InAs, InSb, and HgCdTe alloys. Journal of Applied Physics, 2007, 101, 113104.	2.5	19
2	High intensity light propagation in InAs. Applied Physics Letters, 2006, 89, 161108.	3.3	8
3	Spin lifetimes of electrons injected into GaAs and GaN. Applied Physics Letters, 2003, 83, 1761-1763.	3.3	109
4	Irradiance and temperature dependence of the charge carrier lifetimes in bulk Hg0.6Cd0.4Te. Applied Physics Letters, 2003, 83, 78-80.	3.3	0
5	Full-band-structure calculation of Shockleyâ€“Readâ€“Hall recombination rates in InAs. Journal of Applied Physics, 2001, 90, 848-851.	2.5	29
6	Below band-gap optical absorption in semiconductor alloys. Journal of Applied Physics, 2000, 88, 260-264.	2.5	15
7	Two-photon absorption in GaN, GaInN, and GaAlN alloys. Applied Physics Letters, 2000, 77, 355-357.	3.3	29
8	Direct gap in ordered silicon carbon alloys. Applied Physics Letters, 1999, 75, 3153-3155.	3.3	7
9	Logarithmic approximation for the energy band in nonparabolic semiconductors. Journal of Applied Physics, 1998, 83, 7668-7671.	2.5	7
10	Bandstructure effect on high-field transport in GaN and GaAlN. Applied Physics Letters, 1997, 71, 1999-2001.	3.3	53
11	Accurate calculation of Auger rates in infrared materials. Journal of Applied Physics, 1997, 82, 5540-5546.	2.5	23
12	Electronic structure, absorption coefficient, and auger rate in HgCdTe and thallium-based alloys. Journal of Electronic Materials, 1997, 26, 571-577.	2.2	8
13	Near band edge absorption spectra of narrowâ€gap IIIâ€“V semiconductor alloys. Journal of Applied Physics, 1996, 80, 4045-4048.	2.5	31
14	Temperature dependence of band gaps in HgCdTe and other semiconductors. Journal of Electronic Materials, 1995, 24, 1121-1125.	2.2	30
15	Transport studies in narrow-gap semiconductors revisited. Journal of Electronic Materials, 1995, 24, 641-646.	2.2	16
16	Electron mobility in Hg0.78Cd0.22Te alloy. Journal of Applied Physics, 1994, 75, 7904-7909.	2.5	12
17	Selfâ€consistent calculation of intervalley deformation potentials in GaAs and Ge. Journal of Applied Physics, 1993, 74, 2117-2119.	2.5	14
18	Cleavage energies in semiconductors. Journal of Applied Physics, 1990, 67, 6175-6178.	2.5	22

#	Article	IF	Citations
19	Semiconductor surface sublimation energies and atom-atom interactions. Physical Review Letters, 1990, 64, 2531-2534.	7.8	14
20	Highâ€field transport in semiconductors based on eigenvalue solution to Boltzmann equation. Applied Physics Letters, 1989, 55, 1002-1004.	3.3	15
21	Materials choice for ballistic transport: Group velocities and mean free paths calculated from realistic band structures. Applied Physics Letters, 1988, 52, 468-470.	3.3	16
22	Deformation potential and intervalley scattering: Hotâ€electron transistor analysis. Applied Physics Letters, 1988, 53, 1853-1855.	3.3	20
23	Semiconductor alloys for fast thermal sensors. Journal of Applied Physics, 1988, 64, 1530-1532.	2.5	10
24	Ballistic transport in semiconductor alloys. Journal of Applied Physics, 1988, 63, 4540-4547.	2.5	27
25	Velocityâ€field characteristics of IIIâ€V semiconductor alloys: Band structure influences. Journal of Applied Physics, 1987, 61, 1475-1479.	2.5	20
26	Band structures ofSixGe1â^'xalloys. Physical Review B, 1986, 33, 1026-1035.	3.2	83
27	Electronic structure of silicon superlattices. Superlattices and Microstructures, 1985, 1, 209-215.	3.1	3
28	Generalized Brooksâ€™ formula and the electron mobility in SixGe1â^'xalloys. Applied Physics Letters, 1985, 47, 160-162.	3.3	106
29	Electronic structure and impurity-limited electron mobility of silicon superlattices. Physical Review B, 1985, 32, 1027-1036.	3.2	17
30	Theory of silicon superlattices: Electronic structure and enhanced mobility. Journal of Applied Physics, 1983, 54, 1892-1902.	2.5	56